

ZXTP25040DFH

40V SOT23 PNP medium power transistor

Summary

$BV_{CEO} > -40V$

$BV_{ECO} > -3V$;

$I_{C(Cont)} = -3A$

$R_{CE(sat)} = 55\ m\Omega$;

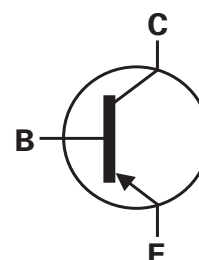
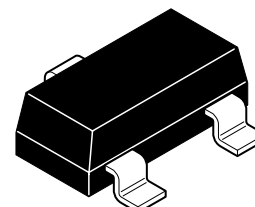
$V_{CE(sat)} < -85mV\ @\ 1A$;

$P_D = 1.25W$

Complementary part number ZXTN25040DFH

Description

Advanced process capability and package design have been used to maximize the power handling and performance of this small outline transistor. The compact size and ratings of this device make it ideally suited to applications where space is at a premium.

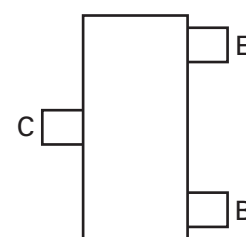


Features

- High power dissipation SOT23 package
- High peak current
- Low saturation voltage
- 7V reverse blocking voltage

Applications

- MOSFET and IGBT gate driving
- DC - DC converters
- Motor drive
- High side driver



Pinout - top view

Ordering information

Device	Reel size (inches)	Tape width	Quantity per reel
ZXTP25040DFHTA	7	8mm	3000

Device marking

024

ZXTP25040DFH

Absolute maximum ratings

Parameter	Symbol	Limit	Unit
Collector-base voltage	V_{CBO}	-45	V
Collector-emitter voltage (forward blocking)	V_{CEO}	-40	V
Emitter-collector voltage (reverse blocking)	V_{ECO}	-3	V
Emitter-base voltage	V_{EBO}	-7	V
Continuous collector current ^(b)	I_C	-3	A
Peak pulse current	I_{CM}	-9	A
Power dissipation at $T_A = 25^\circ\text{C}$ ^(a) linear derating factor	P_D	0.73 5.84	W mW/°C
Power dissipation at $T_A = 25^\circ\text{C}$ ^(b) linear derating factor	P_D	1.05 8.4	W mW/°C
Power dissipation at $T_A = 25^\circ\text{C}$ ^(c) linear derating factor	P_D	1.25 9.6	W mW/°C
Power dissipation at $T_A = 25^\circ\text{C}$ ^(d) linear derating factor	P_D	1.81 14.5	W mW/°C
Operating and storage temperature range	T_j, T_{stg}	-55 to 150	°C

Thermal resistance

Parameter	Symbol	Limit	Unit
Junction to ambient ^(a)	$R_{\theta JA}$	171	°C/W
Junction to ambient ^(b)	$R_{\theta JA}$	119	°C/W
Junction to ambient ^(c)	$R_{\theta JA}$	100	°C/W
Junction to ambient ^(d)	$R_{\theta JA}$	69	°C/W

NOTES:

(a) For a device surface mounted on 15mm x 15mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

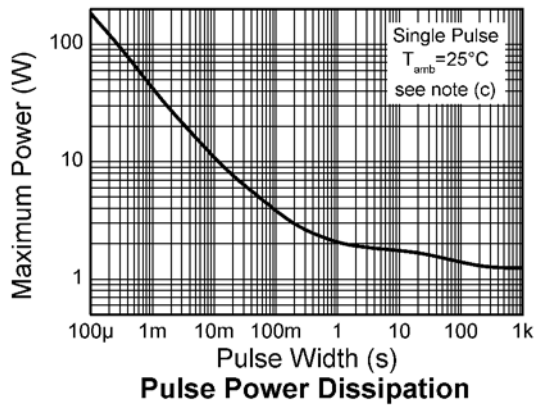
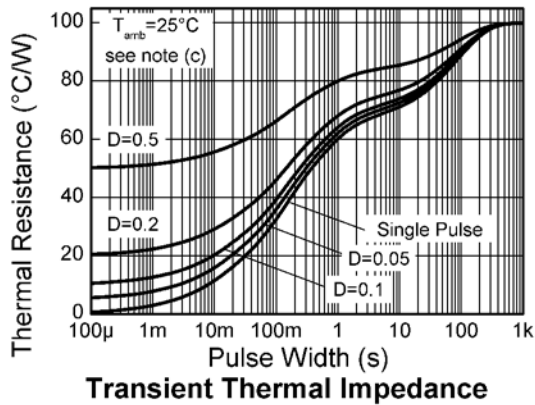
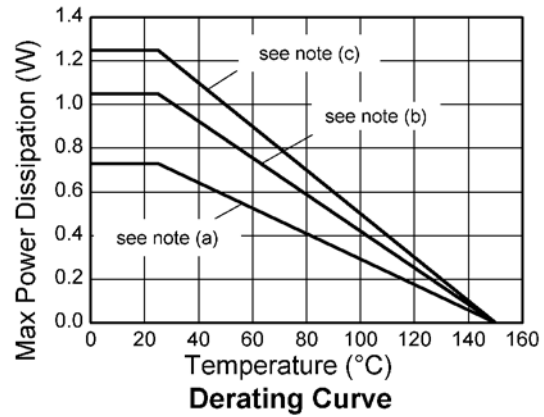
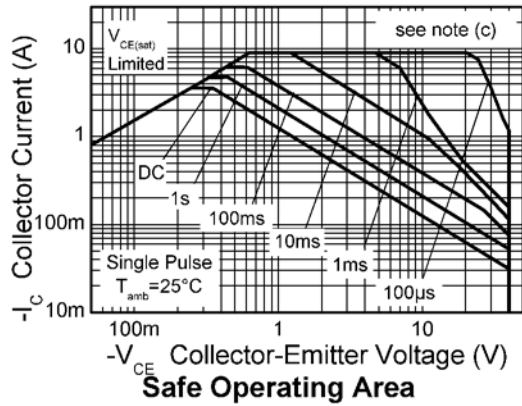
(b) Mounted on 25mm x 25mm x 1.6mm FR4 PCB with a high coverage of single sided 2 oz copper in still air conditions.

(c) Mounted on 50mm x 50mm x 1.6mm FR4 PCB with a high coverage of single sided 2 oz copper in still air conditions.

(d) As (c) above measured at $t < 5\text{sec}$.

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Characteristics



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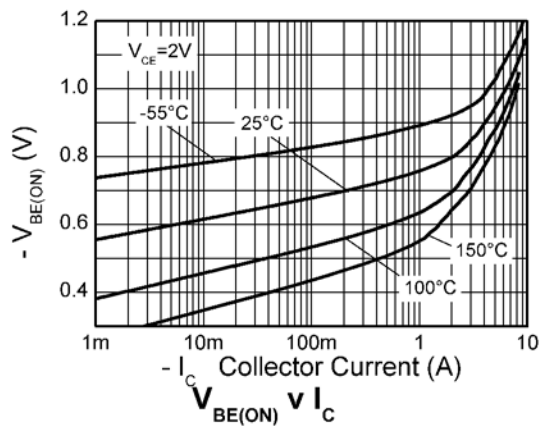
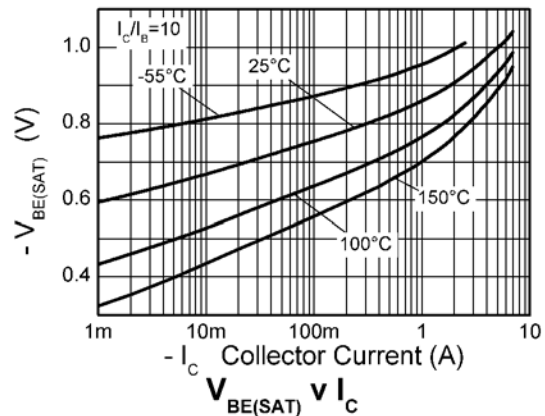
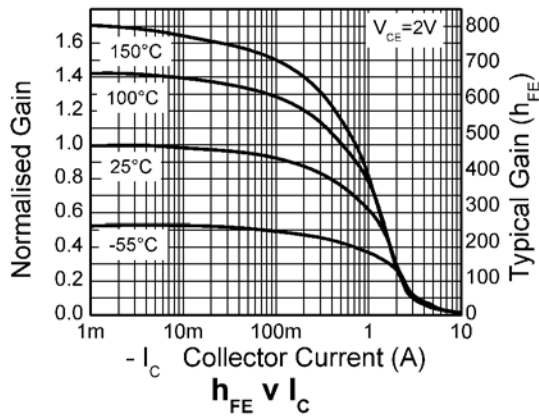
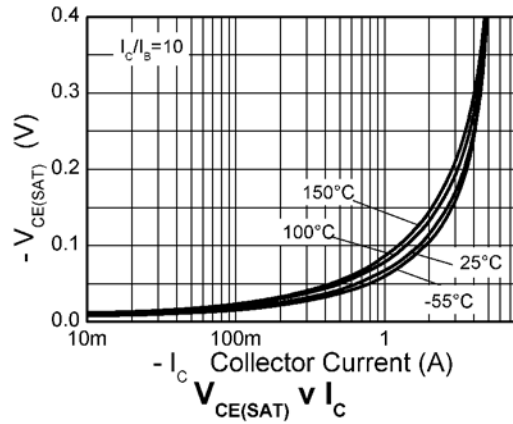
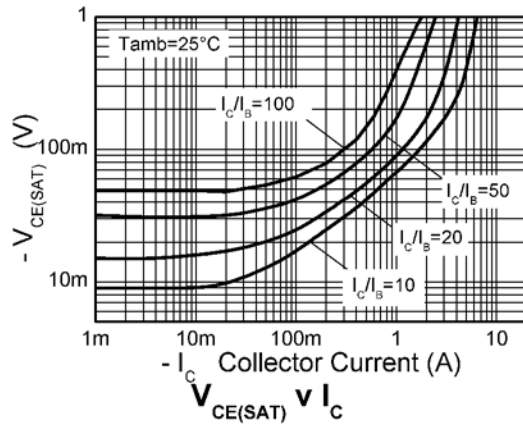
Electrical characteristics (at $T_{AMB} = 25^{\circ}\text{C}$ unless otherwise stated)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CBO}	-45	-75		V	$I_C = -100\mu\text{A}$
Collector-emitter breakdown voltage (base open)	BV_{CEO}	-40	-65		V	$I_C = -10\text{mA}^{(*)}$
Emitter-collector breakdown voltage (reverse blocking)	BV_{ECO}	-3	-8.7		V	$I_E = -100\mu\text{A}^{(*)}$
Emitter-base breakdown voltage	BV_{EBO}	-7	-8.2		V	$I_E = -100\mu\text{A}$
Collector cut-off current	I_{CBO}		<-1	-50 -20	nA μA	$V_{CB} = -36\text{V}$ $V_{CB} = -36\text{V}, T_{amb} = 100^{\circ}\text{C}$
Emitter cut-off current	I_{EBO}		<-1	-50	nA	$V_{EB} = -5.6\text{V}$
Collector-emitter saturation voltage	$V_{CE(sat)}$		-170	-260	mV	$I_C = -1\text{A}, I_B = -20\text{mA}^{(*)}$
			-65	-85	mV	$I_C = -1\text{A}, I_B = -100\text{mA}^{(*)}$
			-165	-220	mV	$I_C = -3\text{A}, I_B = -300\text{mA}^{(*)}$
Base-emitter saturation voltage	$V_{BE(sat)}$		-930	-1000	mV	$I_C = -3\text{A}, I_B = -300\text{mA}^{(*)}$
Base-emitter turn-on voltage	$V_{BE(on)}$		-830	-900	mV	$I_C = -3\text{A}, V_{CE} = -2\text{V}^{(*)}$
Static forward current transfer ratio	h_{FE}	300	450	900		$I_C = -10\text{mA}, V_{CE} = -2\text{V}^{(*)}$
		200	300			$I_C = -1\text{A}, V_{CE} = -2\text{V}^{(*)}$
		30	60			$I_C = -3\text{A}, V_{CE} = -2\text{V}^{(*)}$
Transition frequency	f_T		270		MHz	$I_C = -50\text{mA}, V_{CE} = -10\text{V}$ $f = 100\text{MHz}$
Output capacitance	C_{OBO}		17.4		pF	$V_{CB} = -10\text{V}, f = 1\text{MHz}^{(*)}$
Turn-on time	$t_{(on)}$		75.5		ns	$V_{CC} = -15\text{V}, I_C = -750\text{mA},$ $I_{B1} = I_{B2} = -15\text{mA}.$
Turn-off time	$t_{(off)}$		320		ns	

NOTES:

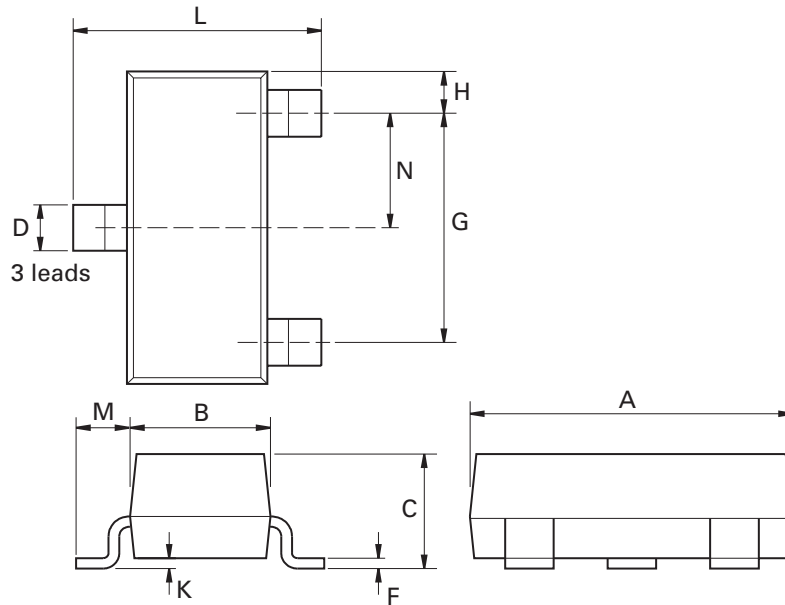
(*) Measured under pulsed conditions. Pulse width $\leq 300\mu\text{s}$; duty cycle $\leq 2\%$.

Typical characteristics



ZXTP25040DFH

Package outline - SOT23



Dim.	Millimeters		Inches		Dim.	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Max.	Max.
A	2.67	3.05	0.105	0.120	H	0.33	0.51	0.013	0.020
B	1.20	1.40	0.047	0.055	K	0.01	0.10	0.0004	0.004
C	-	1.10	-	0.043	L	2.10	2.50	0.083	0.0985
D	0.37	0.53	0.015	0.021	M	0.45	0.64	0.018	0.025
F	0.085	0.15	0.0034	0.0059	N	0.95 NOM		0.0375 NOM	
G	1.90 NOM		0.075 NOM		-	-	-	-	-

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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